

N-channel 60 V, 3.9 mΩ logic level MOSFET in SOT78 5 February 2013 Product data sheet

1. General description

Logic level N-channel MOSFET in SOT78 using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

2. Features and benefits

- High efficiency due to low switching & conduction losses
- Robust construction for demanding applications
- Logic level gate

3. Applications

- Battery-powered tools
- Load switching
- Motor control
- Uninterruptible power supplies

4. Quick reference data

Table 1. Qu	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	130	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	263	W
Static charac	cteristics	·	1	I			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>		-	3.17	3.9	mΩ
Dynamic cha	aracteristics	·		I			
Q _{G(tot)}	total gate charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 48 V;		-	151	-	nC
Q _{GD}	gate-drain charge	<u>Fig. 13; Fig. 14</u>		-	27	-	nC
Avalanche ru	uggedness		1				
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 130 \text{ A}; \text{V}_{sup} \leq 60 \text{V}; \text{R}_{GS} = 50 \Omega; \\ \text{V}_{GS} = 10 \text{V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{array}$		-	-	283	mJ

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain	$2 \circ 4$	
3	S	source	TO-220AB (SOT78)	G G H G H G H G H G H G H G H G H G H G

6. Ordering information

Cable 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN4R2-60PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN4R2-60PL	PSMN4R2-60PL

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

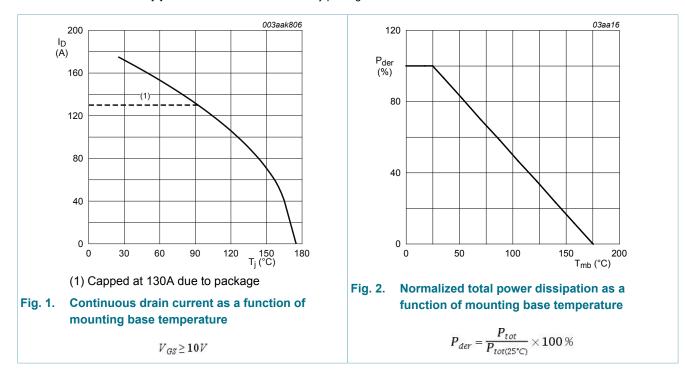
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	130	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>		-	124	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	701	А

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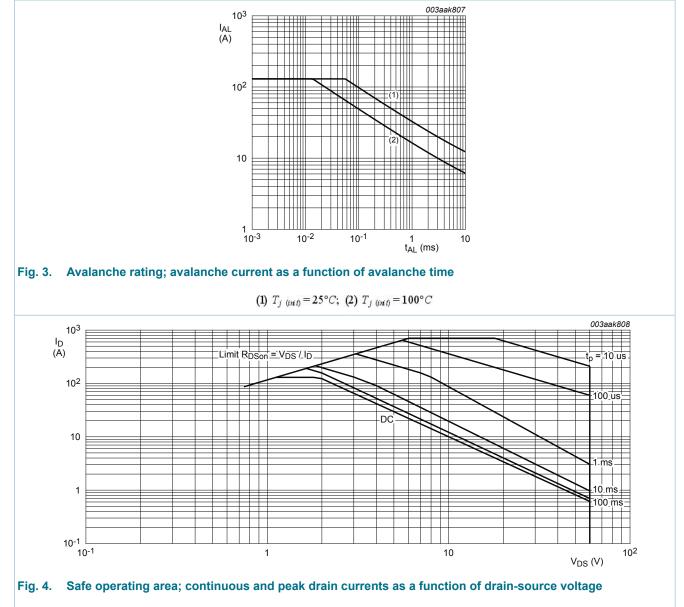
Symbol	Parameter	Conditions		Min	Max	Unit
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	263	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	130	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	701	А
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 130 \text{ A}; V_{sup} \leq 60 \text{V}; \text{R}_{GS} = 50 \Omega; \\ $		-	283	mJ



[1] Continuous current is limited by package.

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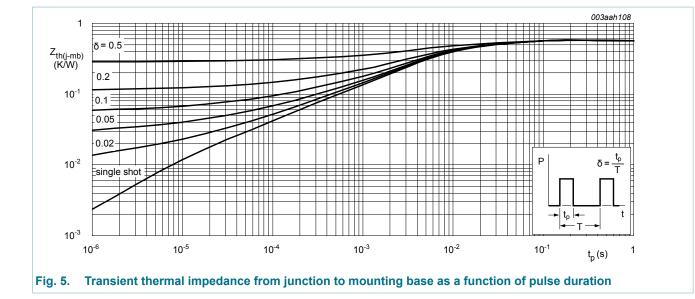
 $T_{mb} = 25^{\circ}C; I_{DM}$ is a single pulse

9. Thermal characteristics

Table 6. The	able 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit		
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	0.49	0.57	K/W		
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air		-	60	-	K/W		

Table 6. Thermal characteristic

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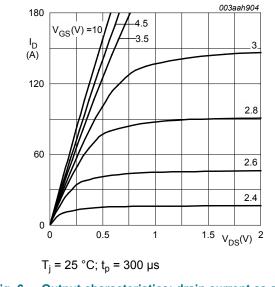


10. Characteristics

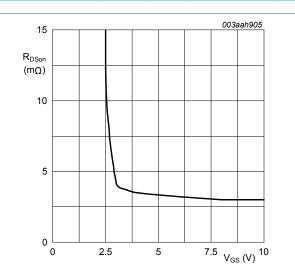
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics	· · ·				_	
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V	
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	-	V	
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V	
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9	0.5	-	-	V	
I _{DSS} drain leakage cu	I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.06	1	μA
	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA	
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	3.6	4.3	mΩ	
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	3.17	3.9	mΩ	
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	8.6	mΩ	
R _G	gate resistance	f = 1 MHz	0.35	0.7	1.4	Ω	

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic cl	haracteristics	· · · · · · · · · · · · · · · · · · ·				
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 10 V; Fig. 13; Fig. 14	-	151	-	nC
		I _D = 25 A; V _{DS} = 48 V; V _{GS} = 5 V; Fig. 13; Fig. 14	-	72	-	nC
Q _{GS}	gate-source charge	I_D = 25 A; V_{DS} = 48 V; V_{GS} = 10 V;	-	20	-	nC
Q _{GD}	gate-drain charge	Fig. 13; Fig. 14	-	27	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>	-	8533	-	pF
C _{oss}	output capacitance		-	703	-	pF
C _{rss}	reverse transfer capacitance		-	357	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R _L = 1.8 Ω; V _{GS} = 5 V;	-	47	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	97	-	ns
t _{d(off)}	turn-off delay time		-	84	-	ns
t _f	fall time		-	73	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V;	-	40	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	59	-	nC







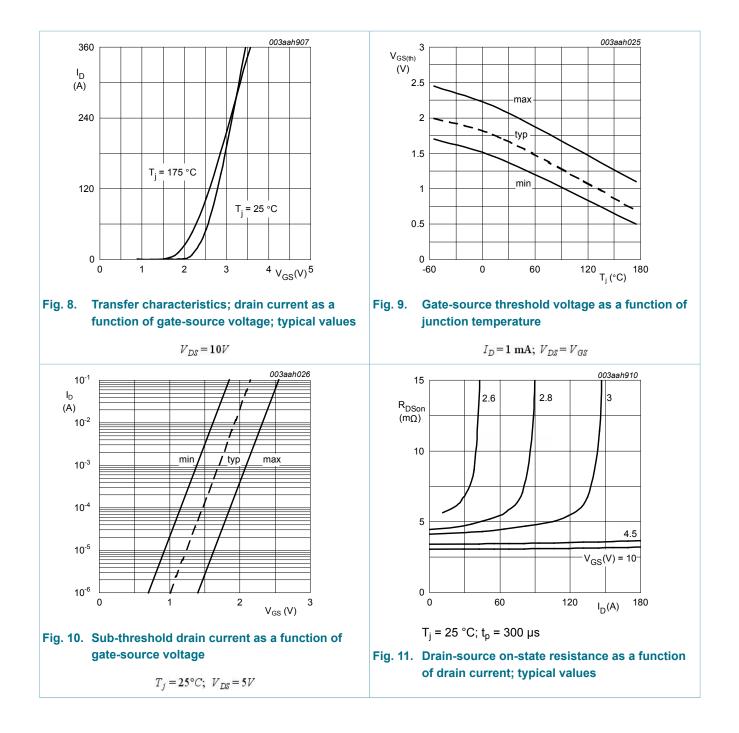


 $T_j = 25^{\circ}C; \ I_D = 25A$

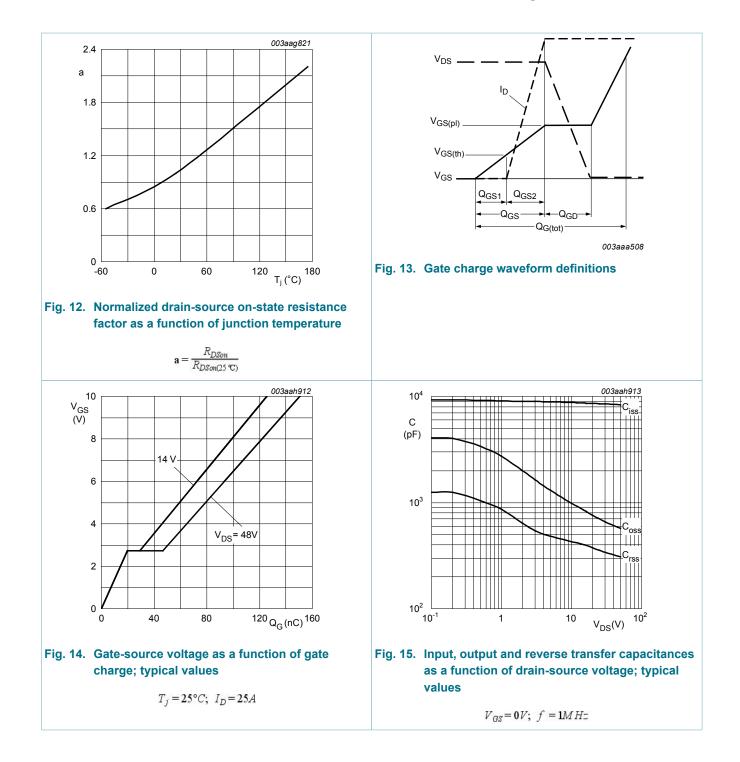
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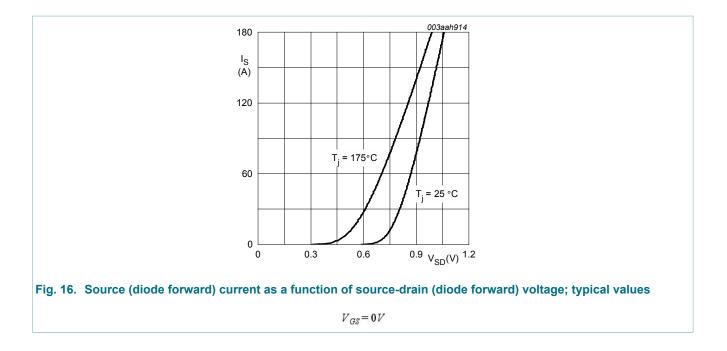


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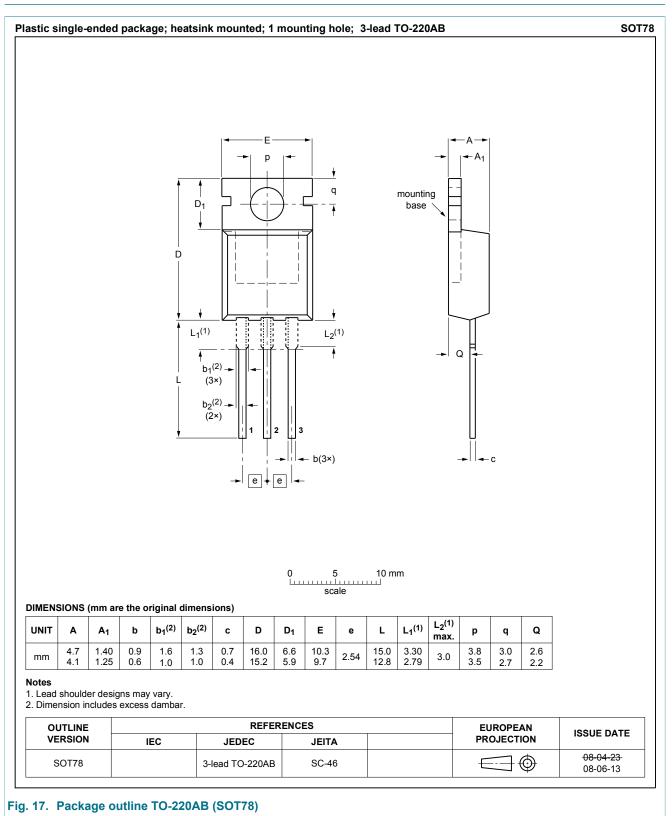
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11. Package outline



PSMN4R2-60PL

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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